Optoelectronics: Light Emitting Diodes

Optoelectronics

light emitting diode
laser diode
solar cell
photo detectors

communications, memory (DVD), displays, printing, bar-code readers, solar energy, lighting, laser surgery, measurement, guidance, spectroscopy, LiFi

Photo detectors

Intrinsic semiconductor $\sigma = e(\mu_n n + \mu_p p)$ (used in copiers)

Unbiased pn junction - like a solar cell

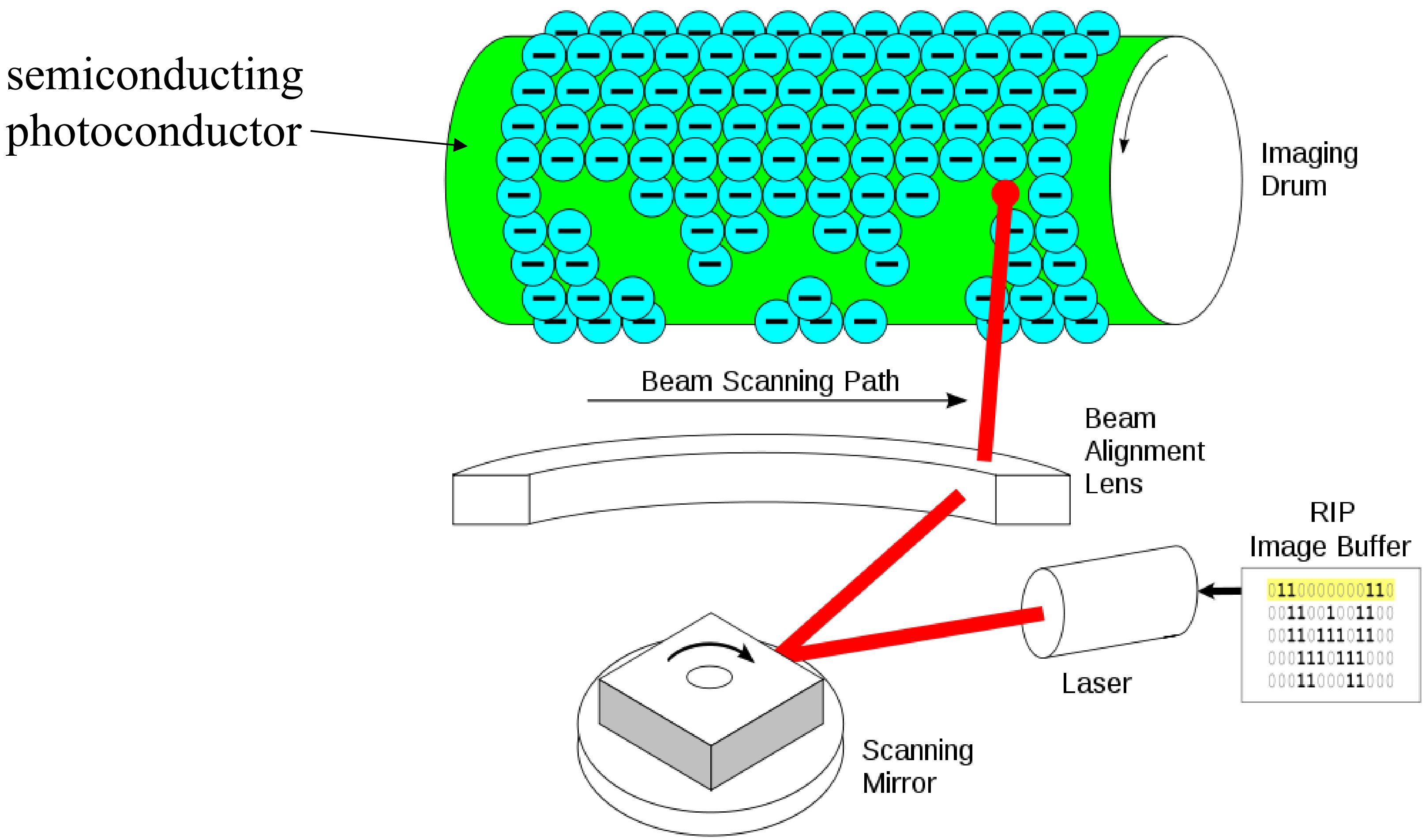
Reverse biased pn junction - smaller capacitance, higher speed, less noise

Phototransistor - light injects carriers into the base. This forward biases the emitter base junction. High responsivity.

Ambient light detectors.

Active Pixel sensors for automated parking and gesture control (uses time-of-flight to image in 3-D).

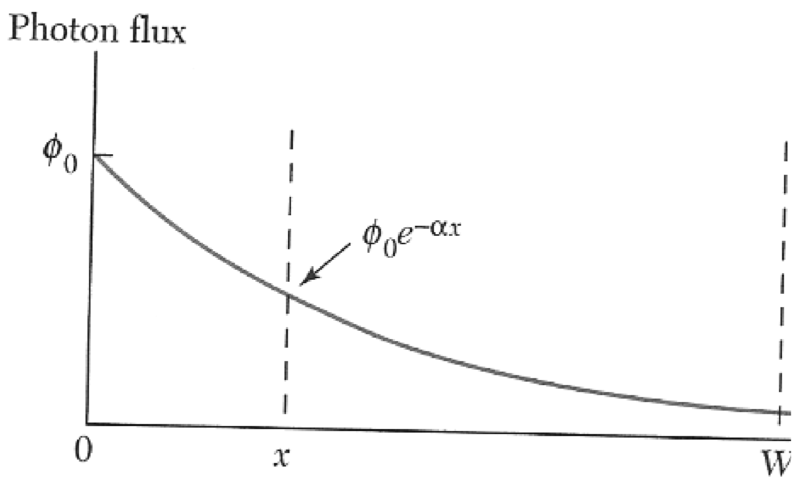
Laser printer



https://en.wikipedia.org/wiki/Laser_printing

Absorption

Photon flux: $\Phi(x) = \Phi_0 e^{-\alpha x}$

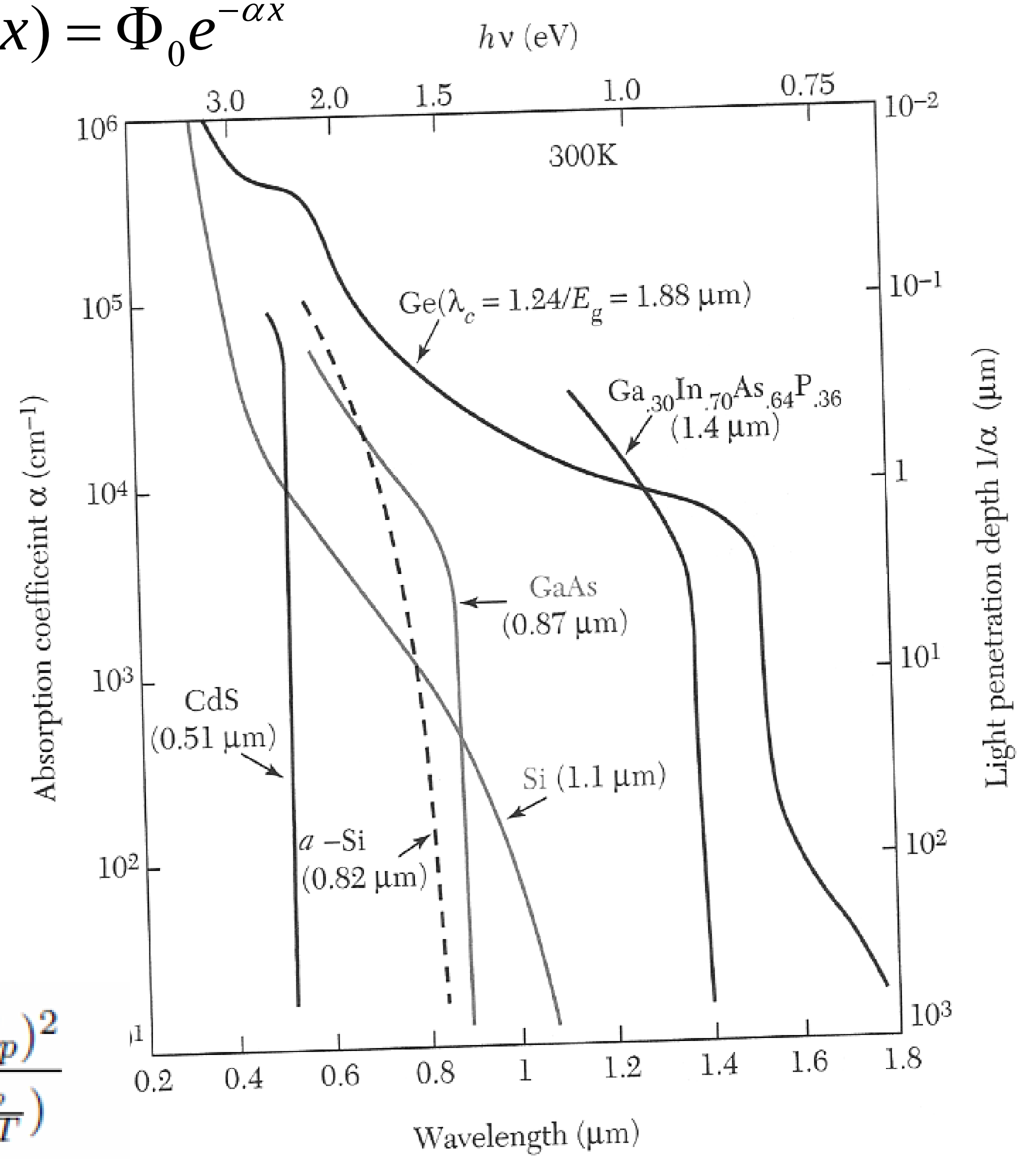


Sharp absorption edge for direct bandgap materials

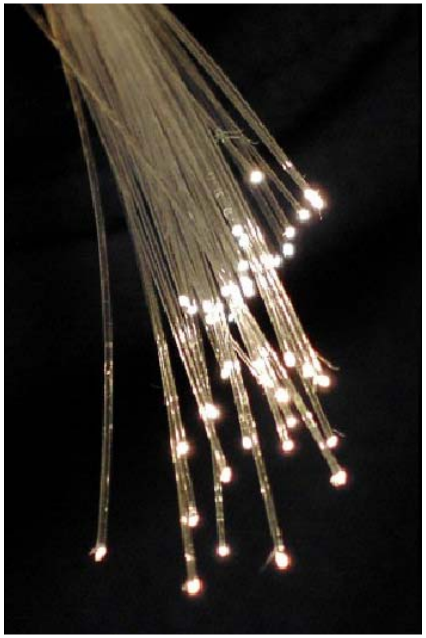
$$\alpha \approx 3.5 \times 10^6 \left(\frac{m_r^*}{m_0}\right)^{3/2} \frac{\sqrt{\hbar\omega - E_g}}{\hbar\omega} \quad \text{cm}^{-1}$$

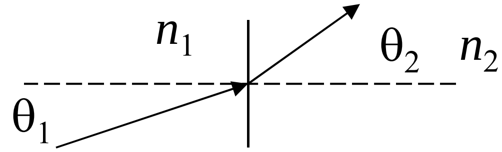
direct bandgap indirect bandgap

$$\alpha \propto \frac{(h\nu - E_g + E_p)^2}{exp(\frac{E_p}{k_B T}) - 1} + \frac{(h\nu - E_g - E_p)^2}{1 - exp(-\frac{E_p}{k_B T})}$$

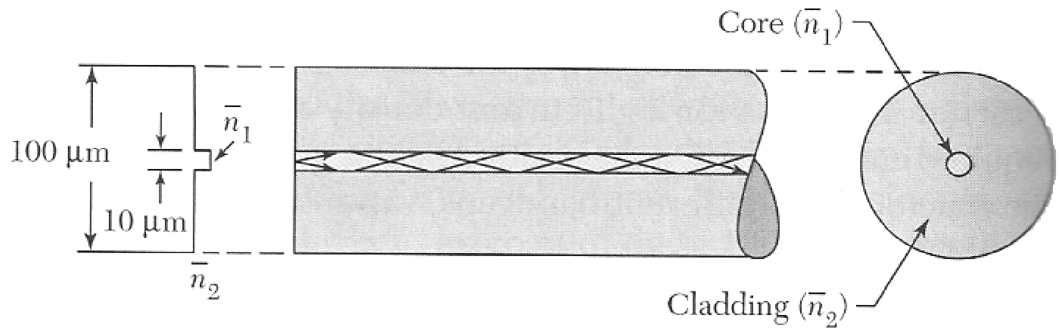


Confinement of light by total internal reflection

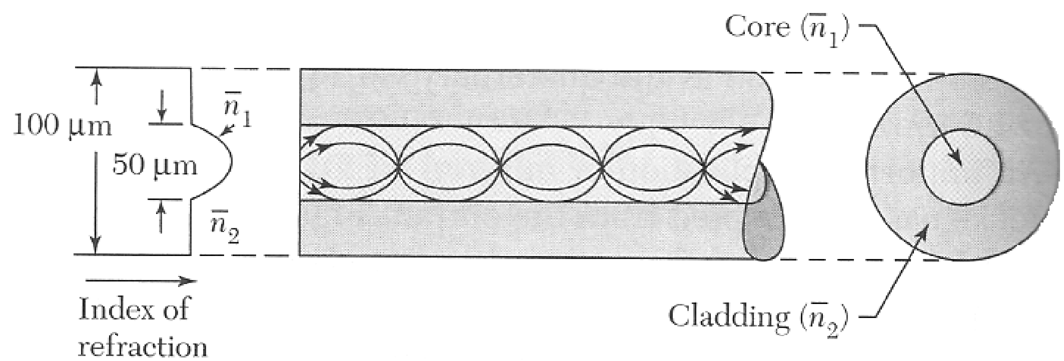




$$n_1 \sin\theta_1 = n_2 \sin\theta_2$$

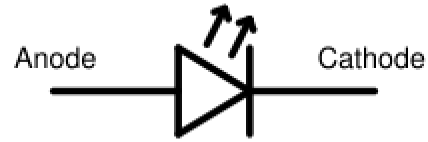


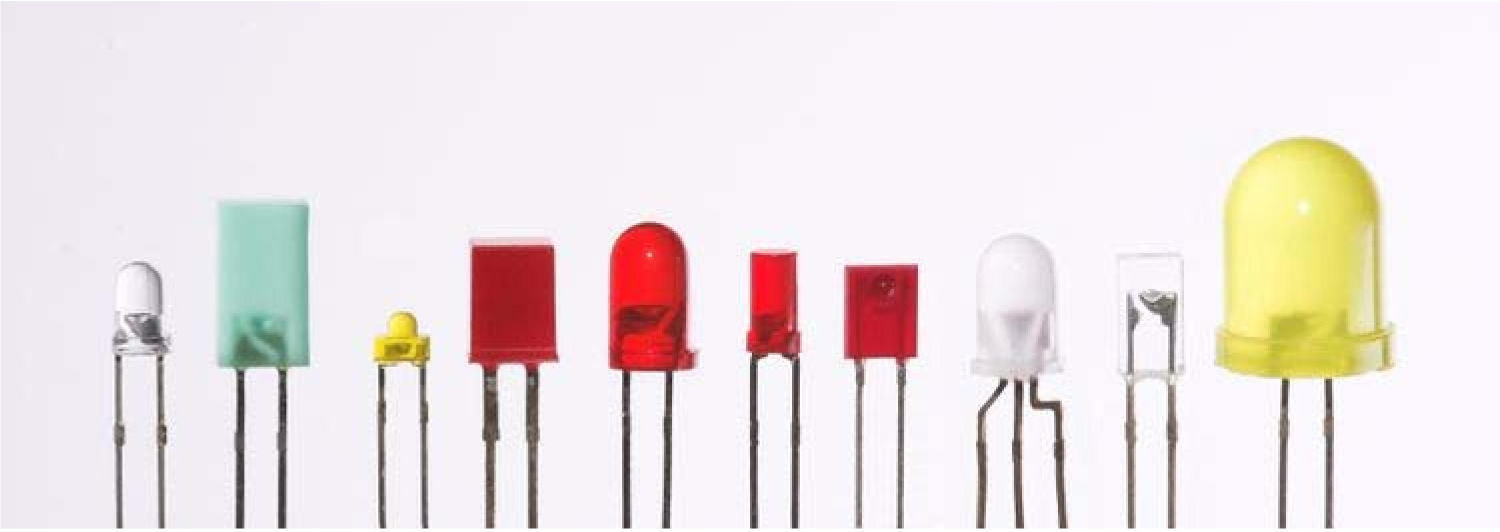
less pulse spreading for parabolically graded fiber

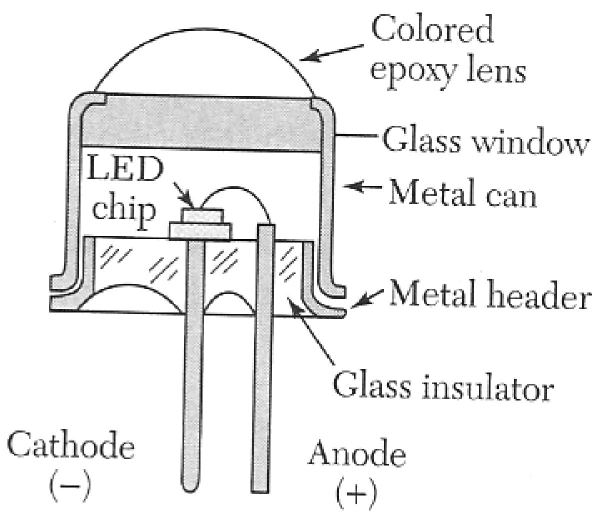


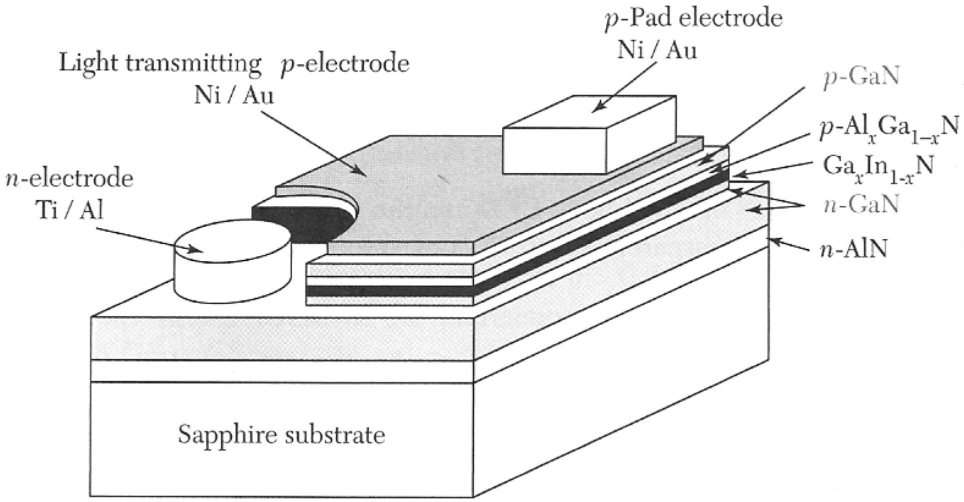
0.6 dB/km at 1.3 μm and 0.2 dB/km at 1.55 μm

Light emitting diodes





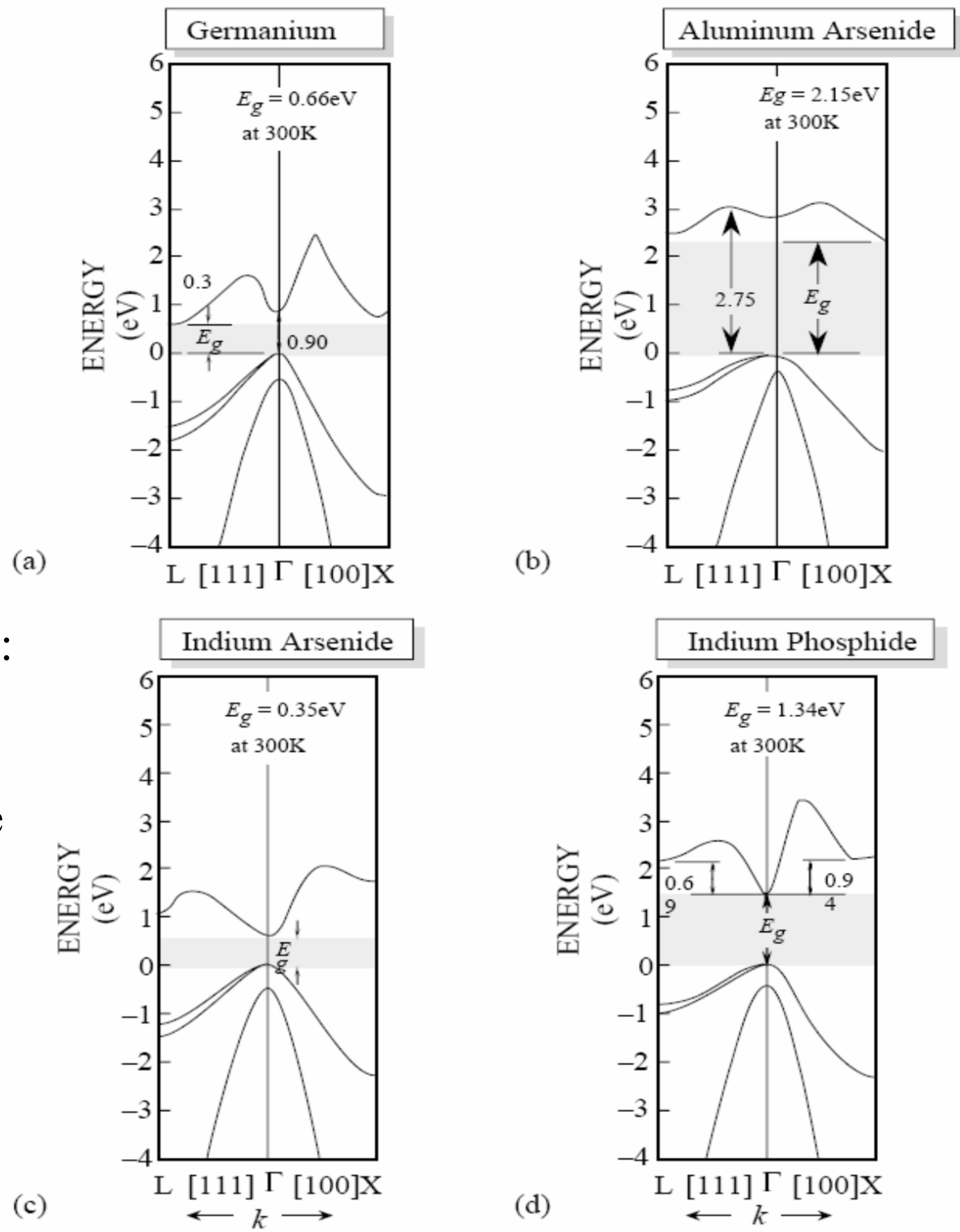




Solid state lighting is efficient.

direct bandgap:
$\Delta k = 0$

photons can be emitted



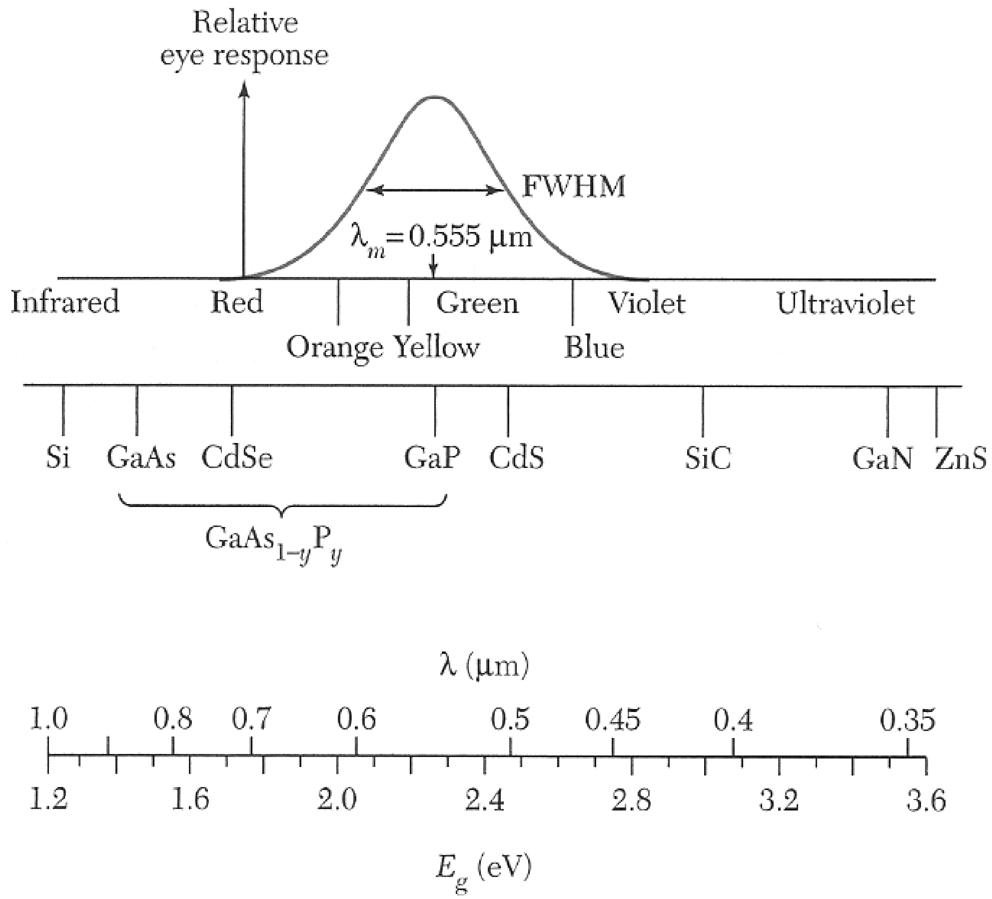
indirect bandgap:
$\Delta k \neq 0$

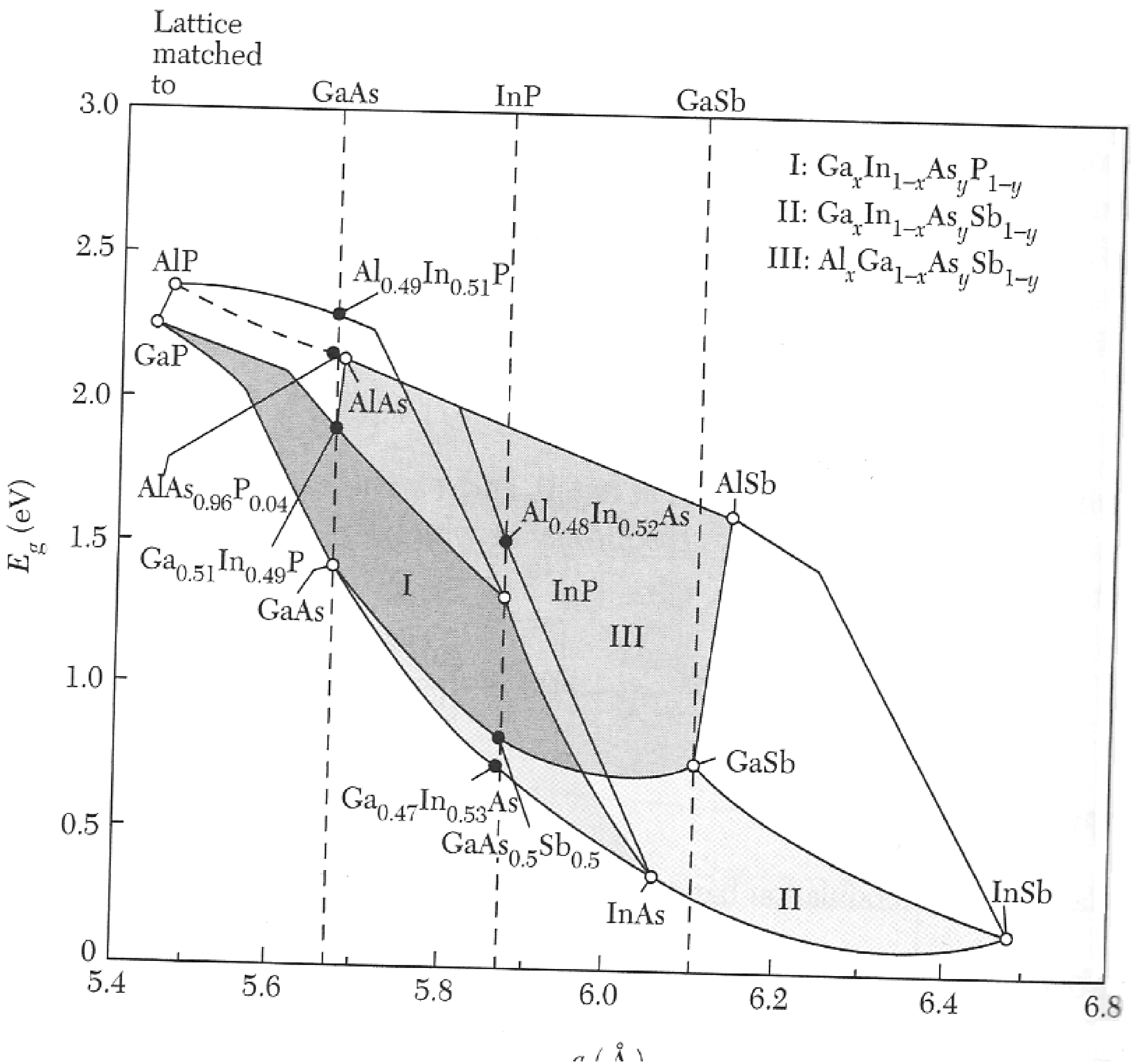
phonons are emitted

Light emitting diodes

TABLE 1 Common III-V materials used to produce LEDs and their emission wavelengths.

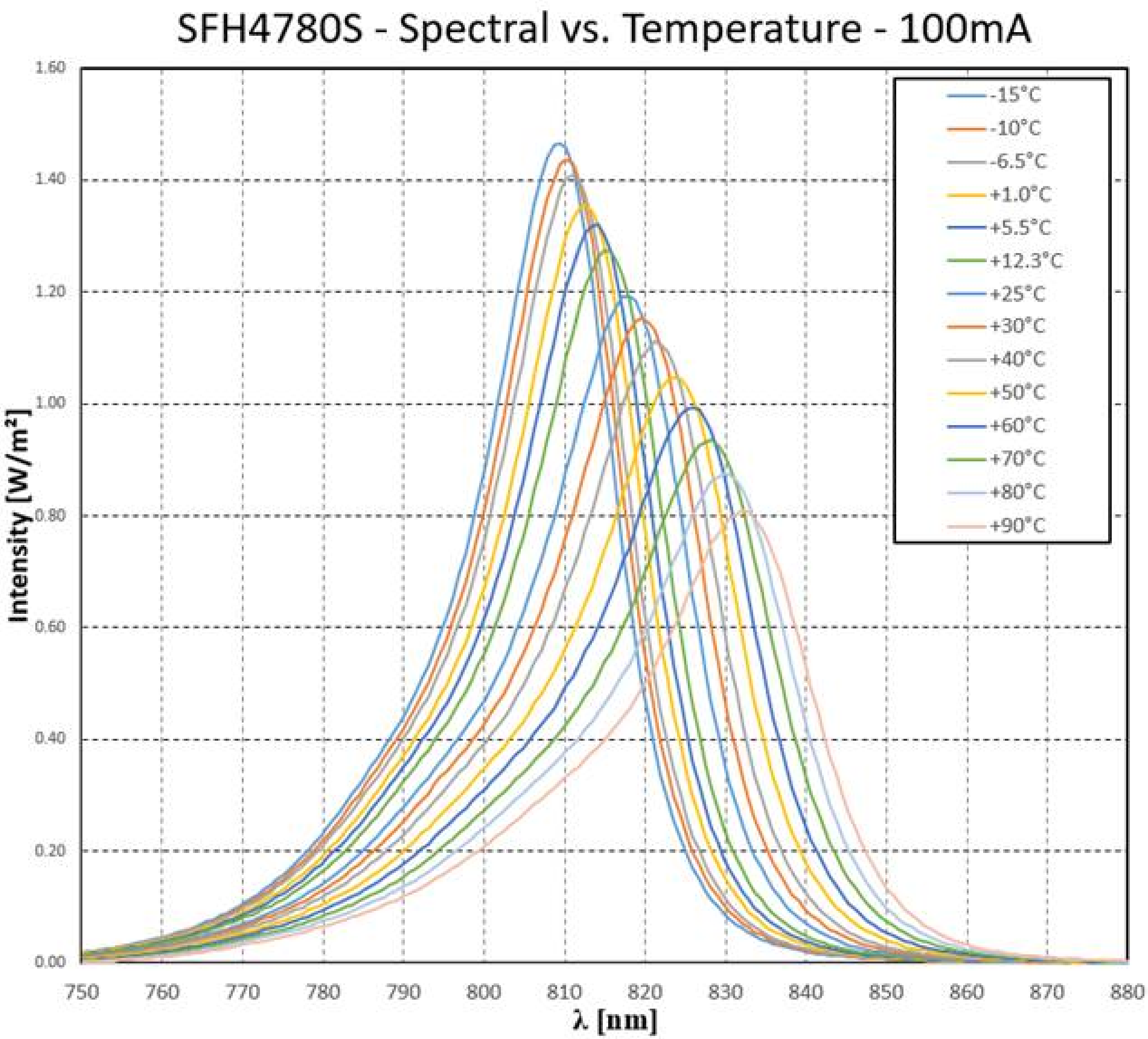
Material	Wavelength (nm)
InAsSbP/InAs	4200
InAs	3800
GaInAsP/GaSb	2000
GaSb	1800
$Ga_xIn_{1-x}As_{1-y}P_y$	1100-1600
$Ga_{0.47}In_{0.53}As$	1550
$Ga_{0.27}In_{0.73}As_{0.63}P_{0.37}$	1300
GaAs:Er,InP:Er	1540
Si:C	1300
GaAs:Yb,InP:Yb	1000
$Al_xGa_{1-x}As$:Si	650-940
GaAs:Si	940
$Al_{0.11}Ga_{0.89}As$:Si	830
$Al_{0.4}Ga_{0.6}As$:Si	650
$GaAs_{0.6}P_{0.4}$	660
$GaAs_{0.4}P_{0.6}$	620
$GaAs_{0.15}P_{0.85}$	590
$(Al_xGa_{1-x})_{0.5}In_{0.5}P$	655
GaP	690
GaP:N	550-570
$Ga_xIn_{1-x}N$	340,430,590
SiC	400-460
BN	260,310,490





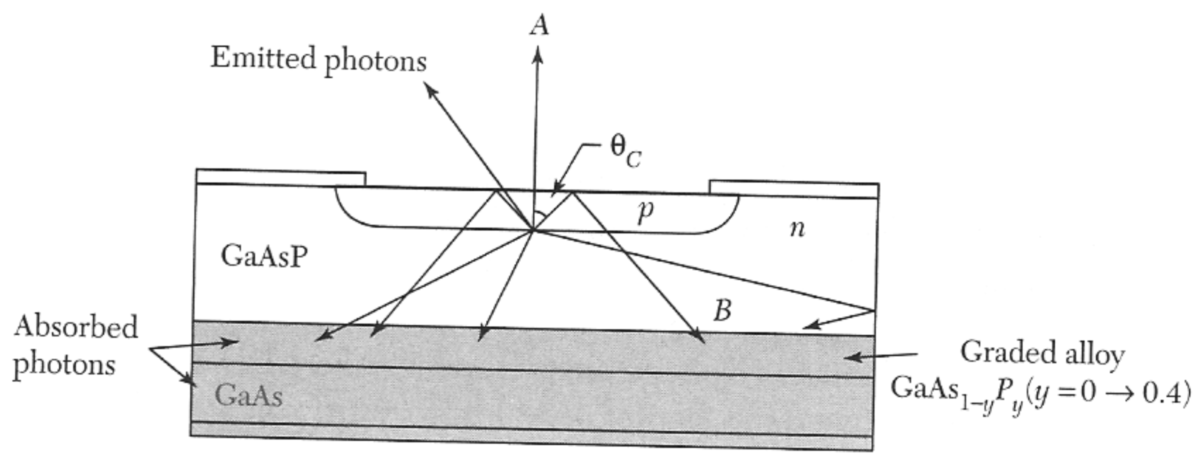
Lattice matched to
GaAs
InP
GaSb
3.0
2.5
2.0
1.5
1.0
0.5
0
E_g (eV)
I: $Ga_xIn_{1-x}As_yP_{1-y}$
II: $Ga_xIn_{1-x}As_ySb_{1-y}$
III: $Al_xGa_{1-x}As_ySb_{1-y}$
AlP
GaP
$Al_{0.49}In_{0.51}P$
AlAs
$AlAs_{0.96}P_{0.04}$
$Ga_{0.51}In_{0.49}P$
GaAs
I
AlSb
$Al_{0.48}In_{0.52}As$
InP
III
GaSb
$Ga_{0.47}In_{0.53}As$
$GaAs_{0.5}Sb_{0.5}$
InAs
II
InSb
5.4
5.6
5.8
6.0
6.2
6.4
6.8

IR LED

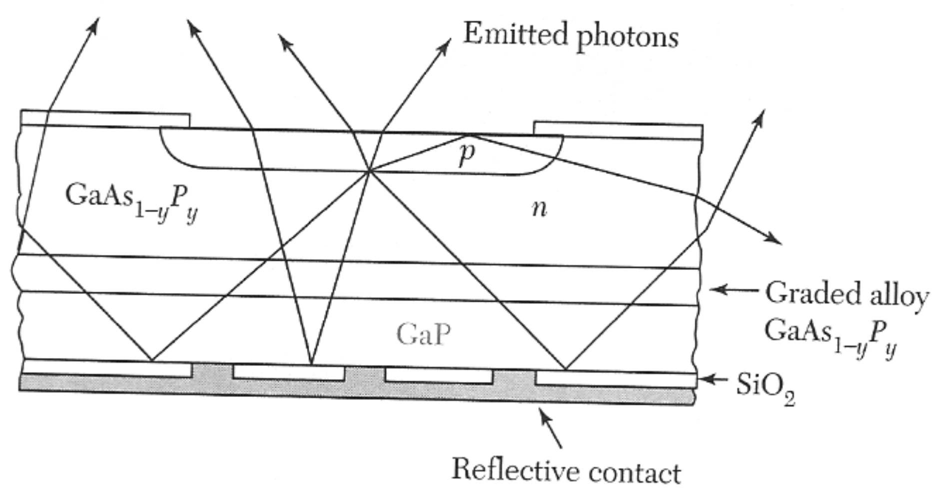


Measurement by Jan Enenkel

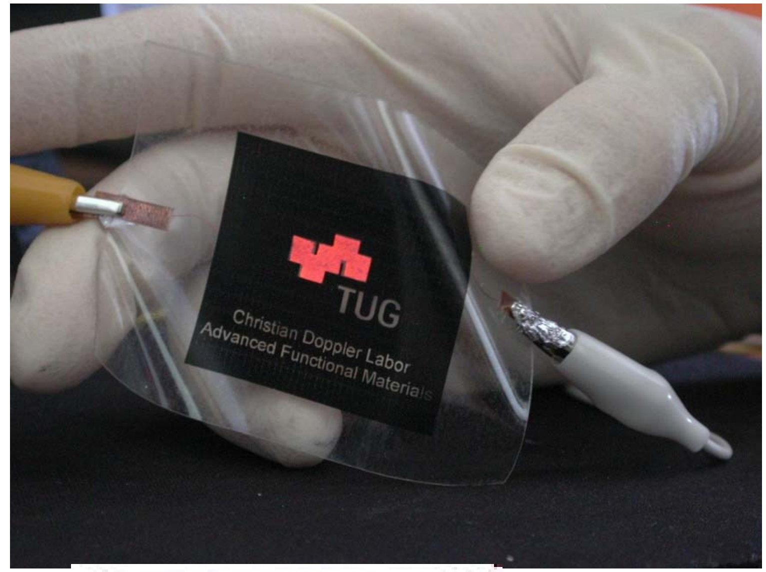
Light emitting diodes

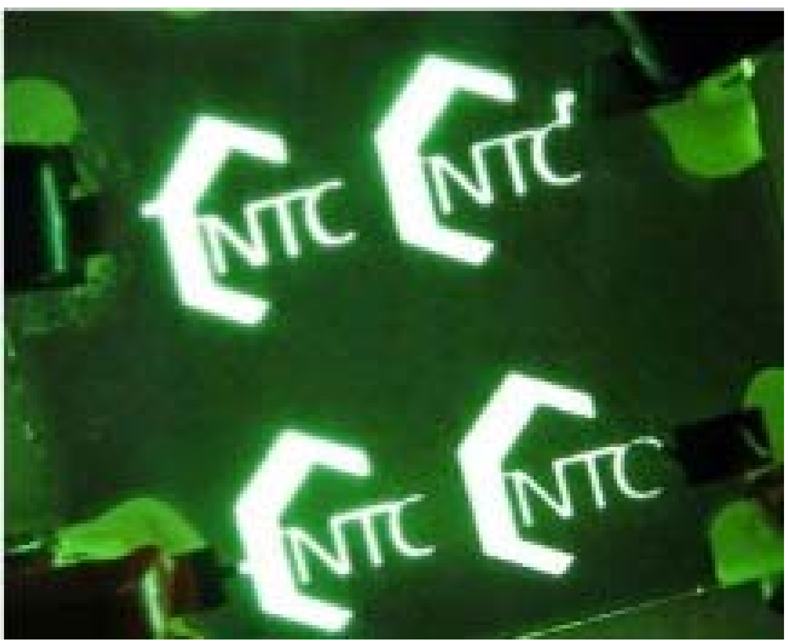


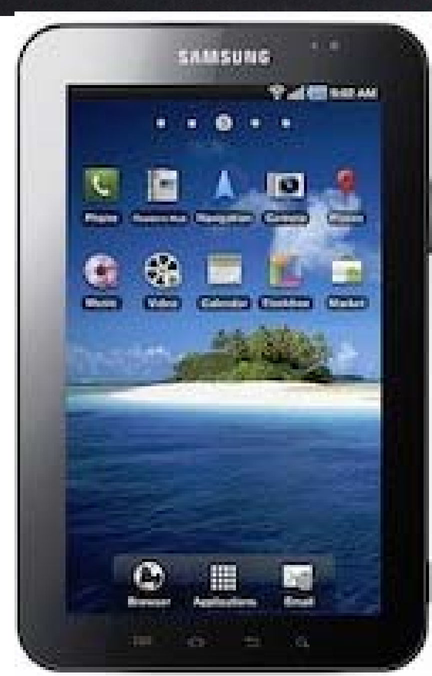
absorption
reflection
total internal reflection



OLEDs







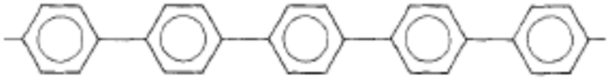
Galaxy Tab

Encapsulation technology

Electroluminescence in poly(p-phenylene)

Prof. Günther Leising

In 1992, Leising et al. for the first time reported on blue electroluminescence from OLEDs containing poly(p-phenylene) (PPP).

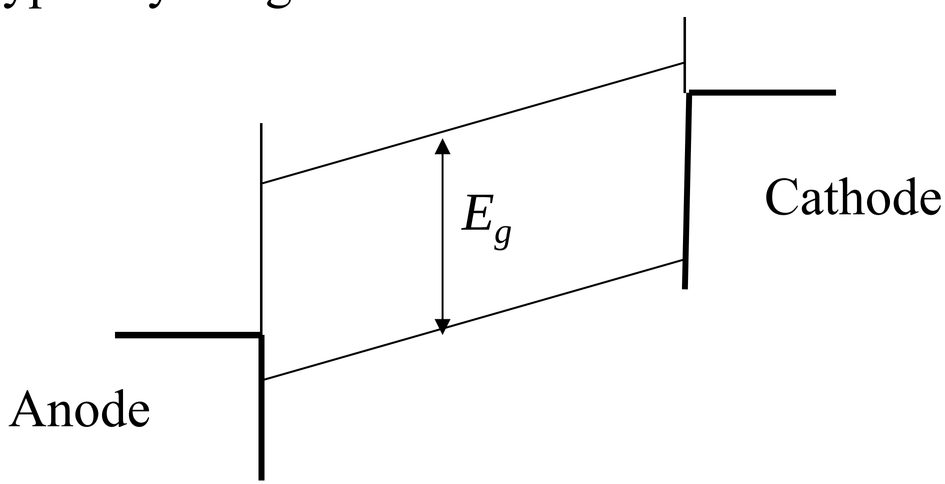


OLEDs

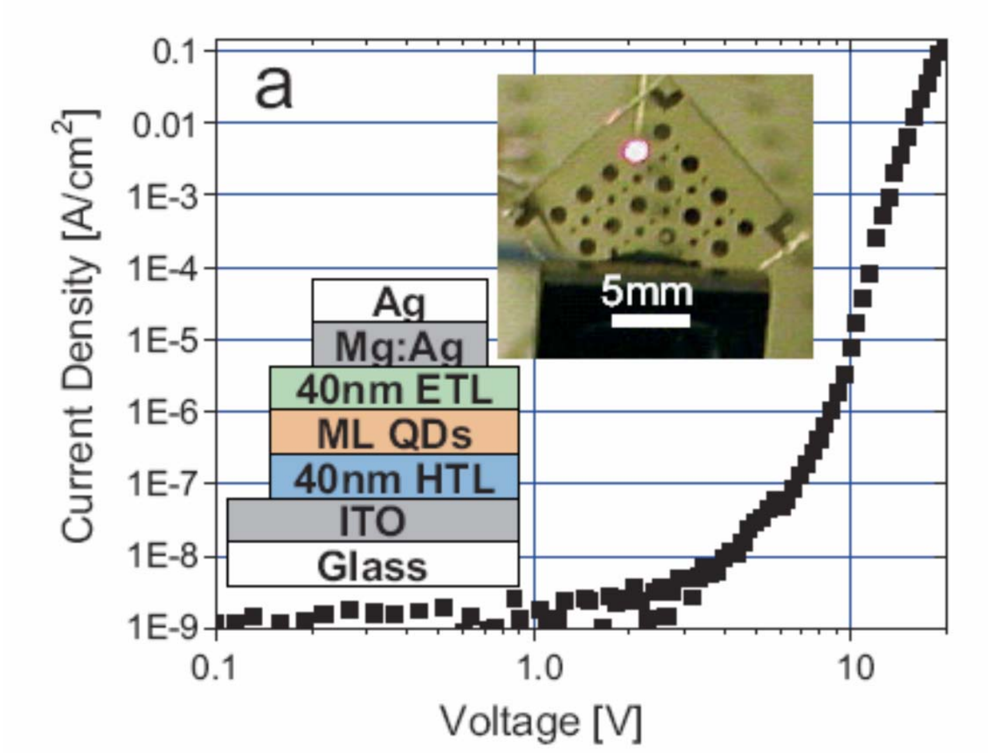
Aluminum cathode
Electron transport layer
Emission layer
Hole transport layer
ITO anode
Glass

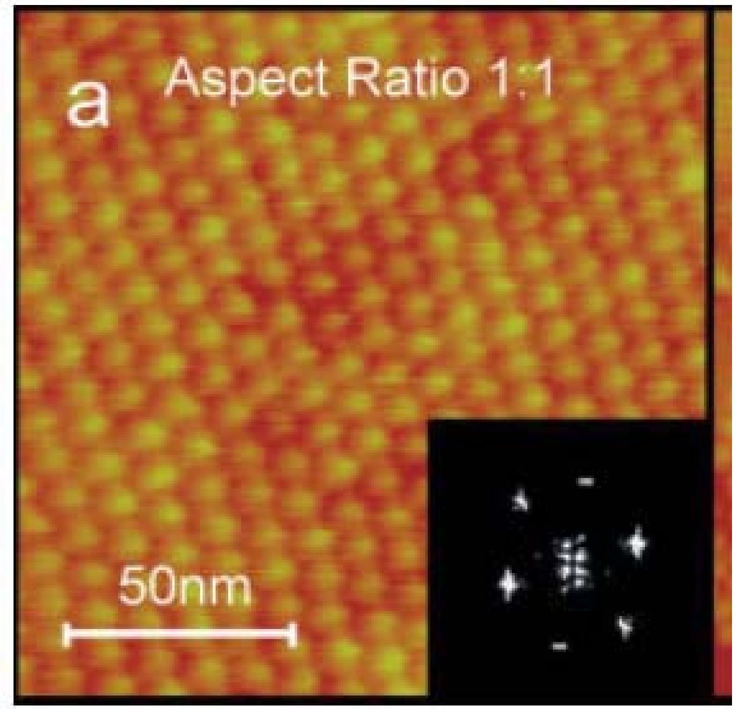
Cathode is typically a low work function material Al, Ca - injects electrons

Anode is typically a high work function material ITO - injects holes



Q-dot LEDs





Coe-Sullivan, et al. Advanced Functional Materials, 10.1002/adfm.200400468

Efficient lighting

Very efficient
Many colors possible
No toxic chemicals

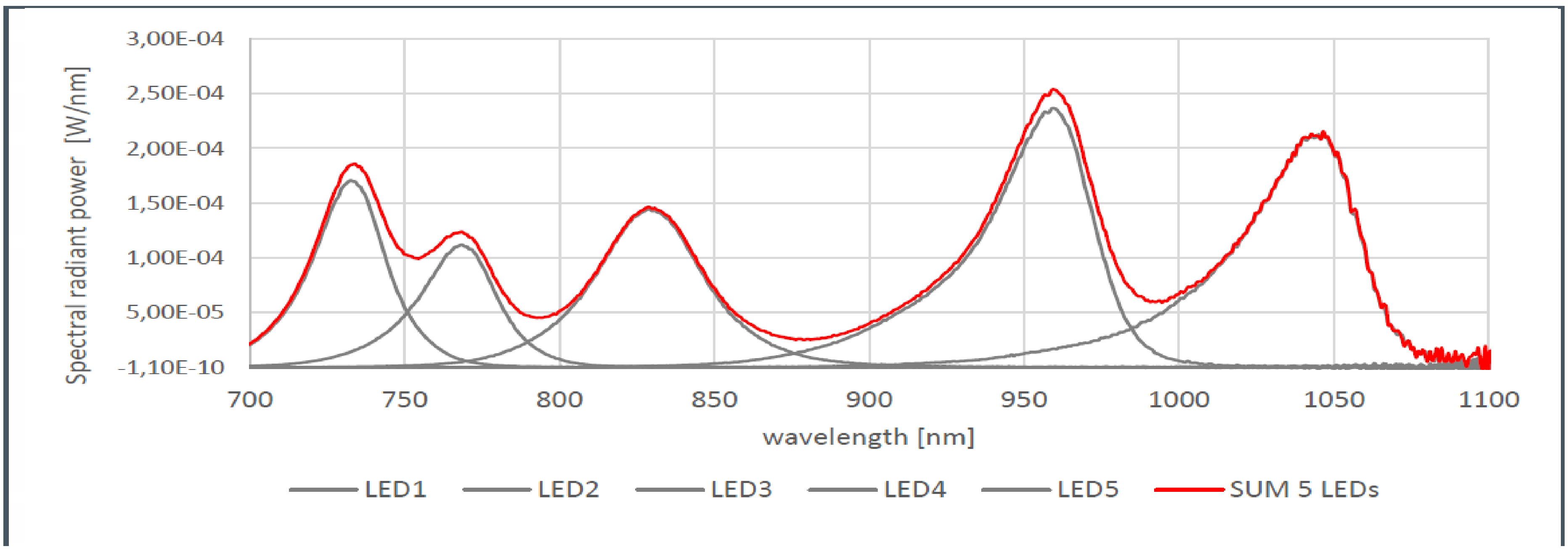
Flexible, transparent, wearable displays

Transparent AMOLED

Folding display

AS7420 64-channel hyperspectral near infrared sensor

Typical LED Spectral Emission at 50mA LED current



AS7420 64-channel hyperspectral near infrared sensor

Typical Spectral Responsivity of Sensor